

## 产品概览

**NTHL040N65S3F: 功率 MOSFET , N 沟道 , SUPERFET® III , FRFET® , 650 V , 65 A , 40 mΩ , TO-247**

欲看完整文档, 请参阅数据表。

技术文档和设计资源 模拟模型 (3) 封装图纸 (1) 数据表 (1)

### 特性

- 700 V @  $T_J = 150^\circ\text{C}$
- Ultra Low Gate Charge (Typ.  $Q_g = 158 \text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss}(\text{eff.}) = 1366 \text{ pF}$ )
- Excellent body diode performance (low  $Q_{rr}$ , robust body diode)
- Optimized Capacitance
- RoHS Compliant
- 100% Avalanche Tested
- Typ.  $R_{DS}(\text{on}) = 32 \text{ m}\Omega$

### 应用

- Telecommunication
- Cloud system
- Industrial

### 优势

- Higher system reliability at low temperature operation
- Lower switching loss
- Lower switching loss
- Higher system reliability in LLC and Phase shift full bridge circuit
- Lower peak  $V_{ds}$  and lower  $V_{gs}$  oscillation

### 终端产品

- Telecom power
- Server power
- EV charger
- Solar / UPS

## 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DSS}(\text{BR})$ Min (V)	$V_{GS}$ Max (V)	$V_{GS}(\text{th})$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$R_{DS(\text{on})}$ Max @ $V_{GS} = 2.5 \text{ V}$ (mΩ)	$R_{DS(\text{on})}$ Max @ $V_{GS} = 4.5 \text{ V}$ (mΩ)	$R_{DS(\text{on})}$ Max @ $V_{GS} = 10 \text{ V}$ (mΩ)	$Q_g$ Typ @ $V_{GS} = 4.5 \text{ V}$ (nC)	$Q_g$ Typ @ $V_{GS} = 10 \text{ V}$ (nC)	$C_{iss}$ Typ (pF)	Package Type
NTHL040N65S3F	4.7952	Pb-free	Active	N-Channel	Single	650	30	5	65	446	-	-	40	-	158	5940	TO-247-3

欲了解更多信息, 请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

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